PAN	JIT
	SEMI
	CONDUCTOR

### **40V Dual N-Channel Enhancement Mode MOSFET**

Voltage

30 A Current

### Features

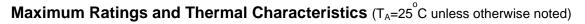
•  $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@12A<12m\Omega$ 

40 V

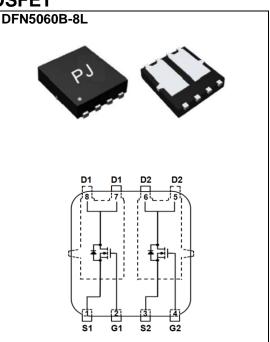
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@4.5V, I<sub>D</sub>@8A<16mΩ</li>
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### **Mechanical Data**

- Case : DFN5060B-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0035 ounces, 0.092 grams



PARAMETE	R	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	40		
Gate-Source Voltage		V <sub>GS</sub>	<u>+20</u>	V	
	T <sub>C</sub> =25°C		30		
Continuous Drain Current (Note 4)	T <sub>C</sub> =100°C	I <sub>D</sub>	19	А	
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	100		
	T <sub>C</sub> =25°C		23.8	14/	
Power Dissipation	$T_{C}=100^{\circ}C$	PD	11.9	W	
(Note 4)	T <sub>A</sub> =25°C		8.6	A	
Continuous Drain Current (Note 4)	T <sub>A</sub> =70°C	I <sub>D</sub>	7		
Power Dissipation	T <sub>A</sub> =25°C	D.	2.0	14/	
	T <sub>A</sub> =70°C	Po	1.4	W	
Single Pulse Avalanche Energy (Note 6)		E <sub>AS</sub>	62	mJ	
Operating Junction and Storage Te	T <sub>J</sub> ,T <sub>STG</sub>	-55~175	°C		
(Note 4.5)	Junction to Case	$R_{ extsf{ heta}JC}$	6.3	°C/W	
Typical Thermal Resistance (Note 4,5)	Junction to Ambient	$R_{ extsf{ heta}JA}$	73.5		
Limited only By Maximum Junction Temperature					





## **Electrical Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	40	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>		1	1.7	2.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =12A	-	10	12	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =8A	-	13	16	mΩ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =40V, $V_{GS}$ =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Qg	V <sub>DS</sub> =20V, I <sub>D</sub> =10A, V <sub>GS</sub> =4.5V <sup>(Note 2,3)</sup>	-	10	-	
Gate-Source Charge	Q <sub>gs</sub>		-	3.5	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	3.6	-	
Input Capacitance	Ciss	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V,	-	1040	-	
Output Capacitance	Coss		-	117	-	pF
Reverse Transfer Capacitance	Crss	f=1MHZ	-	84	-	
Turn-On Delay Time	td <sub>(on)</sub>		-	9.4	-	
Turn-On Rise Time	tr	$V_{DS}=20V, I_{D}=1A,$ $V_{GS}=10V, R_{G}=6\Omega$ (Note 2,3)	-	19	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	66	-	ns
Turn-Off Fall Time	t <sub>f</sub>		-	67	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	I <sub>S</sub>		-	-	30	A
Diode Forward Current Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.7	1	V

NOTES :

- 1. Pulse width
- 2. Essentially independent of operating temperature typical characteristics.
- Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> =25°C.
- 4. The maximum current rating is package limited.
- 5.  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I\_{AS}=35A, V\_{DD}=25V, V\_{GS}=10V, Starting T\_J=25^{\circ}C.
- 7. Guaranteed by design, not subject to production testing.

SEMI CONDUCTOR

PANJ



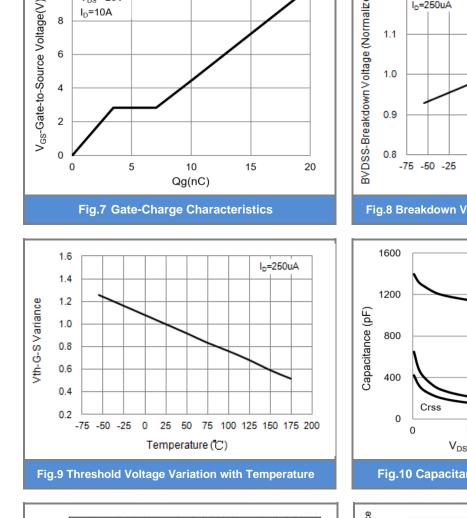
#### **PJQ5848-AU TYPICAL CHARACTERISTIC CURVES** 100 20 V<sub>GS</sub>=10V,8V,6V,5V V<sub>DS</sub>=5V V<sub>GS</sub>=4.5V I<sub>DS</sub>-Drain-to-S ource Current(A) IDS-Drain-to-S ource Current(A) 75 V<sub>GS</sub>=4V 15 V<sub>GS</sub>=3.5V 50 10 V<sub>GS</sub>=3V T<sub>J</sub>=125℃ TJ=25℃ 25 5 V<sub>GS</sub>=2.5V 0 0 0 1 2 3 4 5 0 1 2 5 3 4 V<sub>DS</sub>- Drain-to-Source Voltage(V) V<sub>GS</sub>-Gate-to-Source Voltage(V) **Fig.1 Output Characteristics Fig.2 Transfer Characteristics** 22 2.5 R<sub>bs</sub>(on)- On-Resistance (Normalized) $R_{DS}(on)$ - On-Resistance(m $\Omega$ ) 2.0 18 Vgs=10V, Ip=12A 1.5 V<sub>GS</sub>= 4.5V 14 1.0 V<sub>G8</sub>=4.5V, I<sub>D</sub>=8A $V_{GS}$ = 10V 10 0.5 0.0 6 -75 -50 -25 0 25 50 75 100 125 150 175 200 0 5 10 15 20 Temperature (°C) I<sub>DS</sub>-Drain-to-Source Current(A) Fig.3 On-Resistance vs. Drain Current Fig.4 On-Resistance vs. Junction temperature 10 50 I<sub>D</sub>=6A Isp-Source to Drain Current(A) $R_{DS}(on)$ - On-Resistance(m $\Omega$ ) 40 1 30 T<sub>i</sub>=125℃ 20 Tj=25℃ T<sub>i</sub>=125°C 0.1 T<sub>i</sub>=25°C 10 0 0.01 2 4 6 8 10 0 0.3 0.6 0.9 1.2 V<sub>GS</sub>-Gate-to-Source Voltage(V) V<sub>SD</sub>-Source-to-Drain Voltage(V)

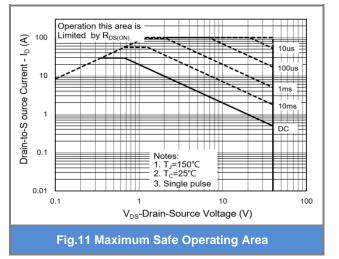
Fig.5 On-Resistance Variation with V<sub>GS</sub>

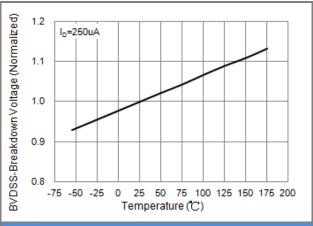
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**TYPICAL CHARACTERISTIC CURVES** 









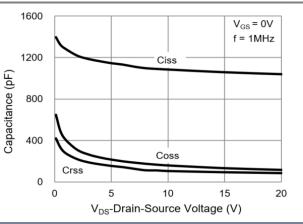
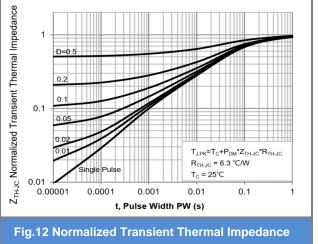


Fig.10 Capacitance vs. Drain-Source Voltage



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**PJQ5848-AU** 

V<sub>DS</sub>= 20V

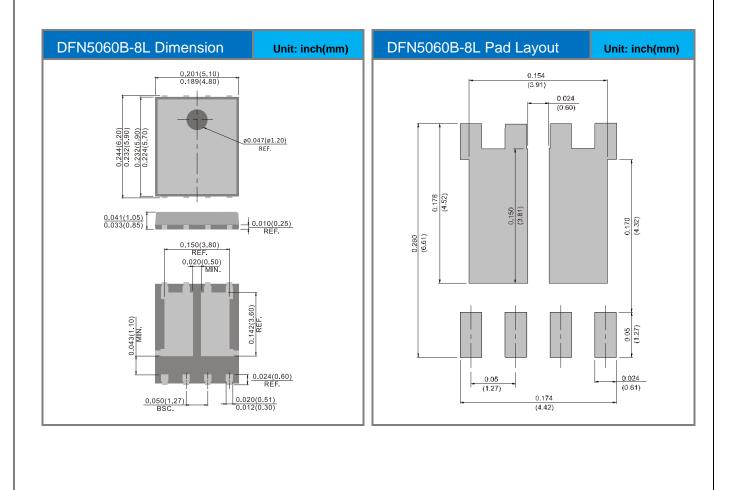




### Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ5848-AU_R2_000A1	DFN5060B-8L	3000pcs / 13" reel	Q5848	Halogen free

### Packaging Information & Mounting Pad Layout





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